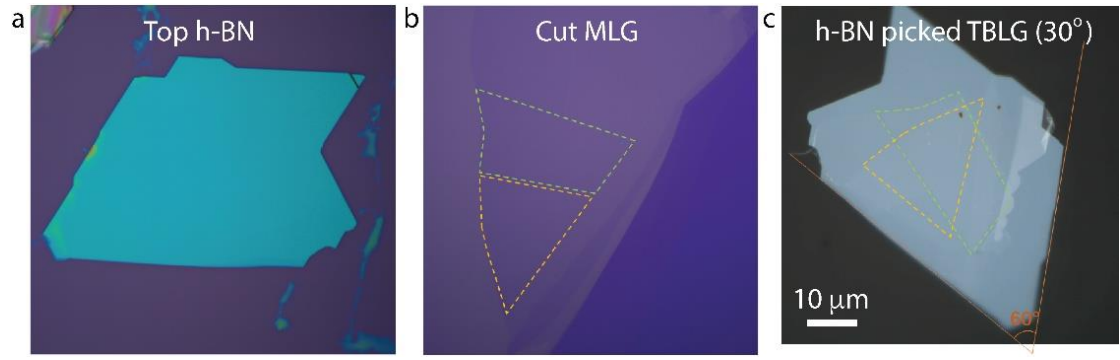


Supplementary Information for
Ferroelectric Polarization in an h-BN-Encapsulated 30°-Twisted
Bilayer–Graphene Heterostructure

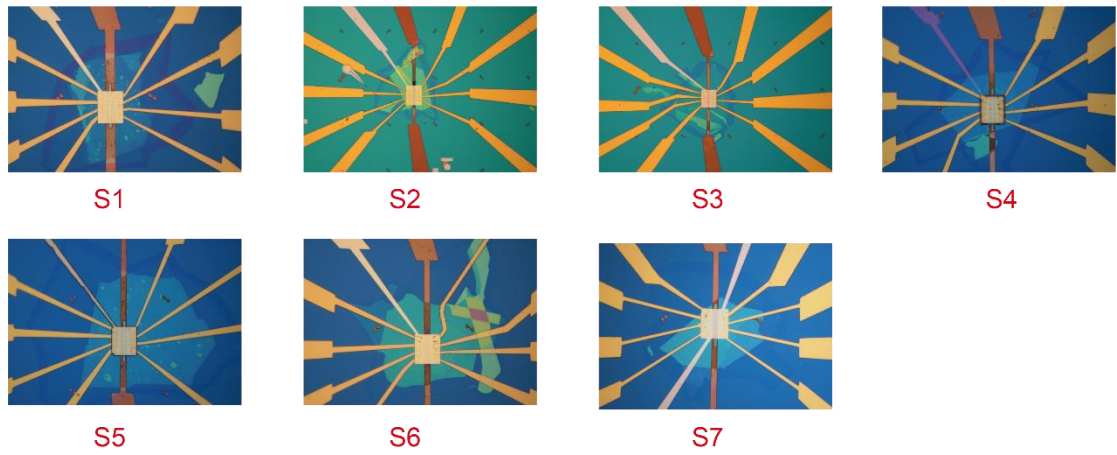
Lingling Ren,^{1,2} Baojuan Dong^{1,2,*}

1 State Key Laboratory of Quantum Optics and Quantum Optics Devices, Institute of
Opto-Electronics, Shanxi University, Taiyuan 030006, China

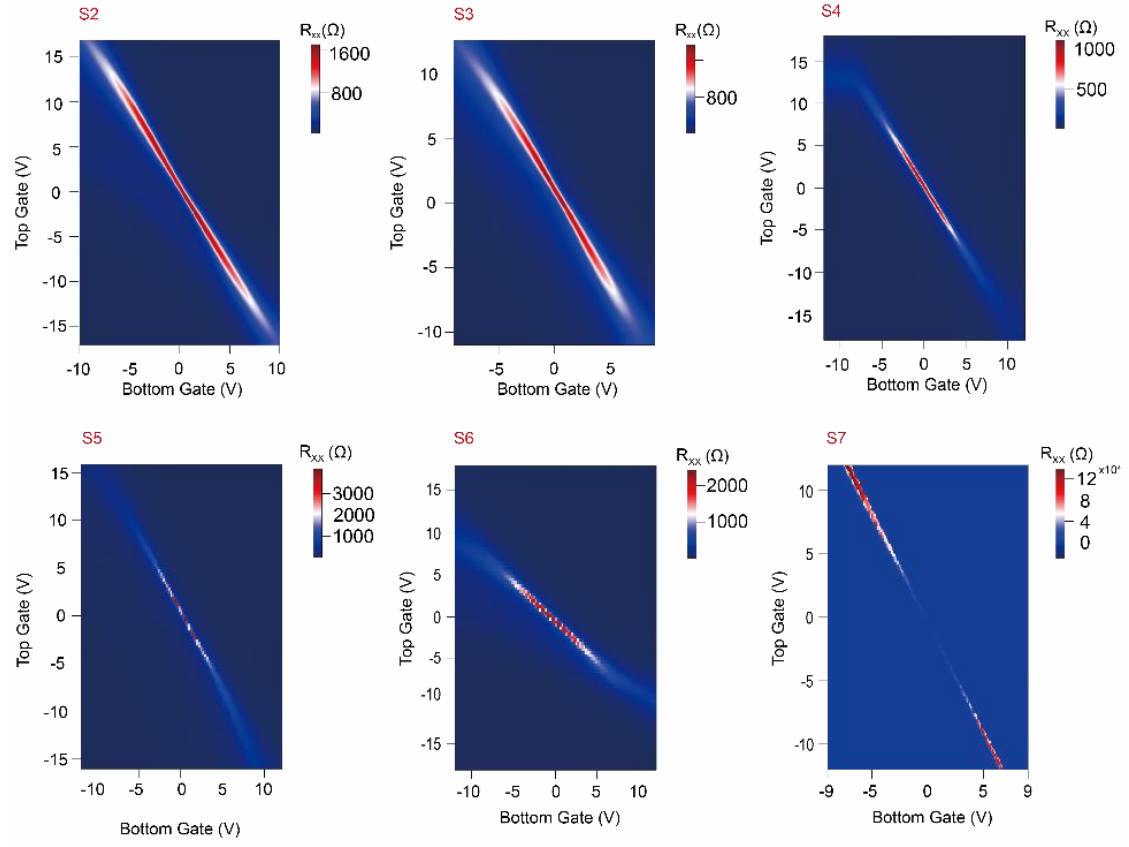
2 Collaborative Innovation Center of Extreme Optics, Shanxi University, Taiyuan 030006,
China



Supplementary Figure S1. Optical images of the several steps of the fabrication process of sample S1.



Supplementary Figure S2. Optical images of samples with the same structure that we fabricated. S1 is the sample mentioned in the main text with ferroelectric polarization, while S2-S7 are samples without ferroelectricity.



Supplementary Figure S3. Dual gate mapping of the samples S2-S7 at 40 mK.